United States Patent [19]

Fletcher et al.

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[54] **HIGH VOLTAGE, HIGH CURRENT SCHOTTKY BARRIER SOLAR CELL**

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[52] **U.S. Cl.** ..... **357/30;** 357/15; 357/16; 136/89 SJ

[58] **Field of Search** 357/15, 16, 30; 136/89

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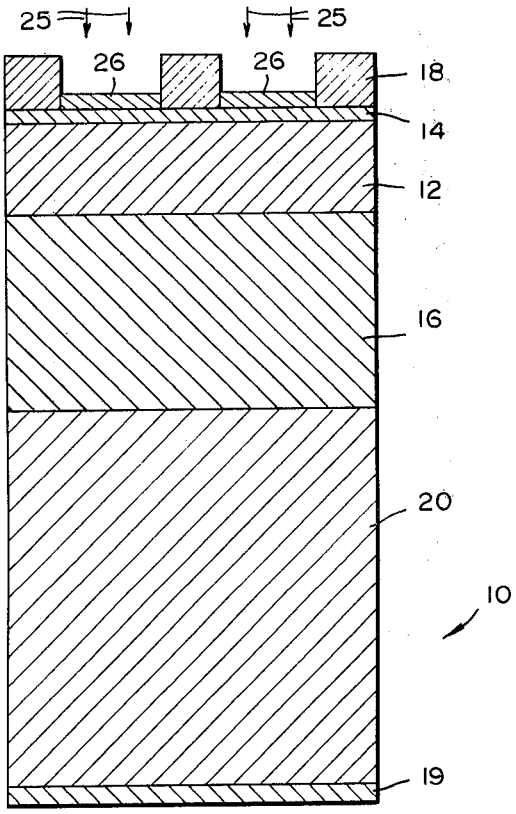
[57] **ABSTRACT**

A Schottky barrier solar cell is disclosed, consisting of a layer of wide band gap semiconductor material such as AlGaAs on which a very thin film of semi-transparent metal is deposited to form a Schottky barrier. The layer of the wide band gap semiconductor material is on top of a layer of narrower band gap semiconductor material, to which one of the cell's contacts may be attached directly or through a substrate. The cell's other contact is a grid structure which is deposited on the thin metal film.

8 Claims, 2 Drawing Figures